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(71)出願人 000000918

花王株式会社

東京都中央区日本橋茅場町1丁目14番10号

(72)発明者 田村 敦司

和歌山市湊1334番地 花王株式会社研究所内

(72)発明者 北村 宏造

和歌山市湊1334番地 花王株式会社研究所内

(74)代理人 100095832

弁理士 細田 芳徳

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(54)【発明の名称】 洗浄剤組成物

(57)【要約】

【課題】金属不純物が付着した半導体基板又は半導体素子の洗浄に優れ、且つシリコンウェハ、配線材料に対する腐食の小さい半導体素子用洗浄剤組成物を提供すること。

【解決手段】リン酸及び／又はその塩を含有し、pHが0.1～6.0である半導体素子用洗浄剤組成物、並びにかかる半導体素子用洗浄剤組成物を用いる半導体素子の洗浄方法。

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(72)Inventor : TAMURA ATSUSHI  
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### (54) LIQUID DETERGENT COMPOSITION

#### (57)Abstract:

**PROBLEM TO BE SOLVED:** To implement improved cleaning for semiconductor elements having metallic impurities deposited thereon by cleaning the semiconductor elements using a liquid detergent composition for semiconductor elements which contains phosphoric acid and a salt thereof and having a predetermined pH range.

**SOLUTION:** Semiconductor elements are cleaned using a liquid detergent composition for semiconductor elements which contains inorganic bases, such as phosphoric acid anhydride (phosphorus pentoxide), orthophosphoric acid (phosphorus acid), hypophosphorus acid (phosphine acid), phosphorus acid (phosphonic acid), polyphosphoric acid and ammonia thereof, and organic bases, such as organic amine, alkanolamine, tetraalkylammonium hydroxide, and whose pH ranges from 0.1 to 6.0. As a result, the cleaning performance of semiconductor substrates or semiconductor elements having metallic impurities deposited thereon can be improved, and the semiconductor substrates and elements are also given the quality of being less corrosive to materials.

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